

Rahul Pandey

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Design and Investigation of Recessed-T-Gate Double Channel HEMT with InGaN Back Barrier for Enhanced Performance. Arabian Journal for Science and Engineering, 2022, 47, 1109-1116.	3.0	12
2	Numerical Study of JAM-GS-GAA FinFET: A Fin Aspect Ratio Optimization for Upgraded Analog and Intermodulation Distortion Performance. Silicon, 2022, 14, 309-321.	3.3	16
3	TCAD investigation of ferroelectric based substrate MOSFET for digital application. Silicon, 2022, 14, 5075-5084.	3.3	10
4	Numerical simulations of 22% efficient all-perovskite tandem solar cell utilizing lead-free and low lead content halide perovskites. Journal of Micromechanics and Microengineering, 2022, 32, 014004.	2.6	14
5	Reliability analysis of cost-efficient CH ₃ NH ₃ PbI ₃ based dopingless tunnel FET. Semiconductor Science and Technology, 2022, 37, 015011.	2.0	3
6	Chemical modulation of conducting polymer gate electrode work function based double gate Mg ₂ Si TFET for gas sensing applications. Journal of Materials Science: Materials in Electronics, 2022, 33, 23927-23936.	2.2	8
7	Numerical simulation of analog metrics and parasitic capacitances of GaAs GS-GAA FinFET for ULSI switching applications. European Physical Journal Plus, 2022, 137, 1.	2.6	6
8	Performance Analysis of Drain Pocket Hetero Gate Dielectric DG-TFET: Solution for Ambipolar Conduction and Enhanced Drive Current. Silicon, 2022, 14, 8097-8107.	3.3	9
9	Ultrascaled 10Ånm Tâ€gate Eâ€mode <sc>InAlN</sc> / <sc>AlN HEMT</sc> with polarized doped buffer for high power microwave applications. International Journal of RF and Microwave Computer-Aided Engineering, 2022, 32, .	1.2	8
10	Sensitivity Analysis of Biomolecule Nanocavity Immobilization in a Dielectric Modulated Triple-Hybrid Metal Gate-All-Around Junctionless NWFET Biosensor for Detecting Various Diseases. Journal of Electronic Materials, 2022, 51, 2236-2247.	2.2	11
11	Mg ₂ Si/Si heterojunction dopingless TFET with reduced random dopant fluctuations for low power applications. Journal of Materials Science: Materials in Electronics, 2022, 33, 6816-6828.	2.2	0
12	Design and simulations of 24.7% efficient silicide on oxide-based electrostatically doped (SILO-ED) carrier selective contact PERC solar cell. , 2022, , 207200.		7
13	RF, linearity and intermodulation distortion analysis with small-signal parameters extraction of tunable bandgap arsenide/antimonide tunneling interfaced JLTFET. Microsystem Technologies, 2022, 28, 2659-2667.	2.0	3
14	Process and device simulations aimed at improving the emitter region performance of silicon PERC solar cells. Journal of Micromechanics and Microengineering, 2022, 32, 025001.	2.6	7
15	Investigation of Carrier Transport Materials for Performance Assessment of Lead-Free Perovskite Solar Cells. IEEE Transactions on Electron Devices, 2022, 69, 3217-3224.	3.0	43
16	Numerical simulations of PbS colloidal quantum dots solar cell with ZnO: PEIE-based electron transport layer. Indian Journal of Physics, 2022, 96, 4203-4208.	1.8	1
17	Optimization of inversion mode and junctionless nanowire MOSFET for improved sensitivity to process induced variability. Applied Nanoscience (Switzerland), 2022, 12, 2161-2168.	3.1	4
18	Detection of biomolecules in dielectric modulated double metal below ferroelectric layer FET with improved sensitivity. Journal of Materials Science: Materials in Electronics, 2022, 33, 13558-13567.	2.2	6

#	ARTICLE	IF	CITATIONS
19	Role of Junctionless Mode in Improving the Photosensitivity of Sub-10 nm Carbon Nanotube/Nanoribbon Field-Effect Phototransistors: Quantum Simulation, Performance Assessment, and Comparison. <i>Nanomaterials</i> , 2022, 12, 1639.	4.1	10
20	22.8% efficient ion implanted PERC solar cell with a roadmap to achieve 23.5% efficiency: A process and device simulation study. <i>Optical Materials</i> , 2022, 128, 112399.	3.6	12
21	Analog/RF Performance and Effect of Temperature on Ferroelectric Layer Improved FET device with Spacer. <i>Silicon</i> , 2022, 14, 12269-12280.	3.3	8
22	Design and parametric optimization of ion-implanted PERC solar cells to achieve 22.8% efficiency: a process and device simulation study. <i>Sustainable Energy and Fuels</i> , 2022, 6, 3249-3262.	4.9	8
23	RF Analysis of a Fully Gate Covered Junctionless FinFET for Improved Performance. , 2022, , .		0
24	Silicide on Oxide Based Carrier Selective Front Contact for 24% Efficient PERC Solar Cell. , 2022, , .		6
25	Linearity Performance of Double Metal Negative Capacitance Field-Effect Transistors: A Numerical Study. , 2022, , .		1
26	Reliability of Sub-20Ånm Black Phosphorus Trench (BP-T) MOSFET in High-Temperature Harsh Environment. <i>Silicon</i> , 2021, 13, 1277-1283.	3.3	3
27	MOS based pseudo-resistors exhibiting Tera Ohms of Incremental Resistance for biomedical applications: Analysis and proof of concept. <i>The Integration VLSI Journal</i> , 2021, 76, 25-39.	2.1	28
28	Gate Oxide Variability Analysis of a Novel 3 nm Truncated Finâ€“FinFET for High Circuitry Performance. <i>Silicon</i> , 2021, 13, 3249-3256.	3.3	12
29	Numerical simulation and proof of concept for performance assessment of cesium based lead-free wide-bandgap halide solar cells. <i>Optical Materials</i> , 2021, 111, 110644.	3.6	20
30	RF Analysis of Double-Gate Junctionless Tunnel FET for Wireless Communication Systems: A Non-quasi Static Approach. <i>Journal of Electronic Materials</i> , 2021, 50, 138-154.	2.2	15
31	Band gap and gate metal engineering of novel hetero-material InAs/GaAs-based JLTFET for improved wireless applications. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 3155-3166.	2.2	6
32	Analog and RF Performance Evaluation of Junctionless Accumulation Mode (JAM) Gate Stack Gate All Around (GS-GAA) FinFET. <i>Silicon</i> , 2021, 13, 919-927.	3.3	41
33	Fin Aspect Ratio Optimization of Novel Junctionless Gate Stack Gate All Around (GS-GAA) FinFET for Analog/RF Applications. <i>Lecture Notes in Electrical Engineering</i> , 2021, , 59-67.	0.4	6
34	TCAD Temperature Analysis of Gate Stack Gate All Around (GS-GAA) FinFET for Improved RF and Wireless Performance. <i>Silicon</i> , 2021, 13, 3741-3753.	3.3	32
35	Enhanced Charge Extraction in Metalâ€“Perovskiteâ€“Metal Back-Contact Solar Cell Structure Through Electrostatic Doping: A Numerical Study. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 1757-1763.	3.0	33
36	Analysis of a Novel Nanoscale Vacuum Channel TF-FinFET. <i>Silicon</i> , 2021, 13, 3257-3269.	3.3	1

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37	Impact of Ferroelectric Oxide Layer on Palladium Silicide Source Electrode based Double-Gate Junctionless TFET. , 2021, , .		0
38	Optimization of Mixed Sn and Pb Perovskite Solar Cell in Terms of Transport Layers and Absorber Layer Thickness Variation. , 2021, , .		5
39	Magnesium Silicide Source Double Palladium Metal Gate TFET for Highly Sensitive Hydrogen Gas Sensor. , 2021, , .		7
40	Technology Computer Aided Design of a Novel Fully Gate Covered Channel Junctionless SOI FinFET for high performance analog application. , 2021, , .		1
41	Thickness Optimisation and Defect Analysis of Wide Bandgap PbS-CQD Solar Cell by SCAPS-1D Simulations. , 2021, , .		2
42	Process voltage temperature analysis of MOS based balanced pseudo-resistors for biomedical analog circuit applications. Circuit World, 2021, , .	0.9	5
43	Numerical Simulation and Optimisation of Wide Bandgap (1.45eV) PbS-CQD Solar Cell for 14% Conversion Efficiency. , 2021, , .		1
44	Silicide Electrode based Electrostatically Doped Back Surface Field in PERC Solar Cell. , 2021, , .		4
45	Impact of Phosphorus Ion Implantation Dose on the Performance of PERC Solar Cell. , 2021, , .		4
46	Assessment of WSe ₂ based BSF layer on CZTSSe solar cell using SCAPS-1D. , 2021, , .		6
47	Design and Optimization of Low Lead Content- Based Mixed Sn and Pb Perovskite Solar Cell for 19.46% Efficiency. , 2021, , .		4
48	Analog Analysis of Novel Ferroelectric-Dual Material Oxide Stack-Double Gate FET. , 2021, , .		0
49	Performance Analysis for SnS- and Sn ₂ S ₃ -Based Back Surface Field CZTSSe Solar Cell: A Simulation Study. Journal of Electronic Materials, 2021, 50, 6318-6328.	2.2	21
50	Impact of interfacial charges on analog and RF performance of Mg ₂ Si source heterojunction double-gate tunnel field effect transistor. Journal of Materials Science: Materials in Electronics, 2021, 32, 23863-23879.	2.2	2
51	A methodical survey on present state of art for electrostatically-doped tunnel FETs and its future prospects. Materials Today: Proceedings, 2021, 45, 5381-5386.	1.8	3
52	Comprehensive device simulation of 23.36% efficient two-terminal perovskite-PbS CQD tandem solar cell for low-cost applications. Scientific Reports, 2021, 11, 19829.	3.3	40
53	Comprehensive device simulation of 16.9% efficient two-terminal PbS-PbS CQD tandem solar cell. Optical Materials, 2021, 122, 111677.	3.6	8
54	Investigations aimed at producing 33% efficient perovskite-silicon tandem solar cells through device simulations. RSC Advances, 2021, 11, 37366-37374.	3.6	34

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55	A Numerical Study of Analog Parameter of Negative Capacitance Field Effect Transistor with Spacer. , 2021, , .		6
56	Source Material-Engineered Charge Plasma based Double Gate TFET for Analog/RF Applications. , 2021, , .		3
57	Numerical simulation of charge transport layer free perovskite solar cell using metal work function shifted contacts. Optik, 2020, 202, 163646.	2.9	32
58	Design Considerations and Capacitance Dependent Parametric Assessment of Gate Metal Engineered SiNW MOSFET for ULSI Switching Applications. Silicon, 2020, 12, 1501-1510.	3.3	5
59	Performance evaluation of linearity and intermodulation distortion of nanoscale GaN-SOI FinFET for RFIC design. AEU - International Journal of Electronics and Communications, 2020, 115, 153052.	2.9	31
60	Numerical simulation and parametric assessment of GaN buffered trench gate MOSFET for low power applications. IET Circuits, Devices and Systems, 2020, 14, 915-922.	1.4	9
61	Challenges faced in running "Train the Trainers" program by industry professionals and possible solutions. Procedia Computer Science, 2020, 172, 427-432.	2.0	0
62	Device simulations: Toward the design of >13% efficient PbS colloidal quantum dot solar cell. Solar Energy, 2020, 207, 893-902.	6.1	88
63	Design and optimization of 26.3% efficient perovskite/FeSi ₂ monolithic tandem solar cell. Journal of Materials Science: Materials in Electronics, 2020, 31, 15218-15224.	2.2	22
64	Impact of Graded Back-Barrier on Linearity of Recessed Gate InAlN/GaN HEMT. , 2020, , .		6
65	TCAD Analysis and Modelling of Gate-Stack Gate All Around Junctionless Silicon NWFET Based Bio-Sensor for Biomedical Application. , 2020, , .		2
66	The Effect of Gate Stack and High- κ Spacer on Device Performance of a Junctionless GAA FinFET. , 2020, , .		12
67	A Low-Power gm-C Filter for Neural Signal Conditioning. , 2020, , .		0
68	Current Reference Circuit Operable at Low Voltages Using Composite MOS Triode Resistor. , 2020, , .		1
69	Sub-10 nm High-k Dielectric SOI-FinFET for HighPerformance Low Power Applications. , 2020, , .		7
70	Rapid detection of biomolecules in a dielectric modulated GaN MOSHEMT. Journal of Materials Science: Materials in Electronics, 2020, 31, 16609-16615.	2.2	24
71	Design and Simulation of ϵ -Si:H/PbS Colloidal Quantum Dots Monolithic Tandem Solar Cell for 12% Efficiency. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000252.	1.8	29
72	Microstates-based resting frontal alpha asymmetry approach for understanding affect and approach/withdrawal behavior. Scientific Reports, 2020, 10, 4228.	3.3	9

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73	A 1.1 \hat{A} ¼W biopotential amplifier based on bulk-driven quasi-floating gate technique with extremely low-value of offset voltage. Analog Integrated Circuits and Signal Processing, 2020, 103, 303-313.	1.4	18
74	Effect of structural and temperature variations on perovskite/Mg2Si based monolithic tandem solar cell structure. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	25
75	Device simulation of 17.3% efficient lead-free all-perovskite tandem solar cell. Solar Energy, 2020, 197, 212-221.	6.1	188
76	Numerical analysis of Mg2Si/Si heterojunction DG-TFET for low power/high performance applications: Impact of non-idealities. Superlattices and Microstructures, 2020, 139, 106397.	3.1	26
77	Conducting Polymer Based Gas Sensor Using PNIN- Gate All Around - Tunnel FET. Silicon, 2020, 12, 2947-2955.	3.3	10
78	Investigation of electrical/analog performance and reliability of gate metal and source pocket engineered DG-TFET. Microsystem Technologies, 2020, , 1.	2.0	3
79	Effect of temperature on analog performance of Mg2Si source heterojunction double gate tunnel field effect transistor. Materials Today: Proceedings, 2020, 28, 1520-1524.	1.8	4
80	A novel source material engineered double gate tunnel field effect transistor for radio frequency integrated circuit applications. Semiconductor Science and Technology, 2020, 35, 105013.	2.0	14
81	Comprehensive Study on the Recent Development of PERC Solar Cell. , 2020, , .		13
82	Performance Evaluation of Lead-free Perovskite Solar Cell with Different Hole/Electron Transport Materials. , 2020, , .		2
83	Influence of SnS and Sn₂S₃ based BSF layers on the performance of CZTSSe solar cell. , 2020, , .		9
84	Device Simulation of Poly (3-Hexylthiophene) HTL Based Single and Double Halide Perovskite Solar Cells. , 2020, , .		1
85	Built-in Reliability Investigation of Gate-Drain Underlapped PNIN-GAA-TFET for Improved Linearity and Reduced Intermodulation Distortion. Lecture Notes in Electrical Engineering, 2020, , 205-213.	0.4	1
86	Impact of metal silicide source electrode on polarity gate induced source in junctionless TFET. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	2.3	20
87	Non-Quasi-Static Small-Signal Modeling of TGRC MOSFET in Parameter Perspective for RF/Microwave Applications. , 2019, , .		0
88	Effect of Temperature on GaAs Junctionless FinFET Using High- \hat{e} Dielectric. , 2019, , .		1
89	Sub-30nm In2O5Sn gate electrode recessed channel MOSFET: A biosensor for early stage diagnostics. Vacuum, 2019, 164, 46-52.	3.5	19
90	Toward the design of monolithic 23.1% efficient hysteresis and moisture free perovskite/c-Si HJ tandem solar cell: a numerical simulation study. Journal of Micromechanics and Microengineering, 2019, 29, 064001.	2.6	38

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91	Designing of CZTSSe Based SnS Thin Film Solar Cell for Improved Conversion Efficiency: A Simulation Study with SCAPS. , 2019, , .		8
92	Numerical Simulations to Understand the Role of DIO Additive in PTB7:PC71BM Solar Cell. , 2019, , .		0
93	Design and Simulation of Novel Perovskite/Mg2Si Based Monolithic Tandem Solar Cell With 25.5% Conversion Efficiency. , 2019, , .		2
94	Carbon Nanotube Recessed Channel (CNT-RC) MOSFET for High Linearity/ULSI Applications. , 2019, , .		2
95	Numerical simulations: Toward the design of 18.6% efficient and stable perovskite solar cell using reduced cerium oxide based ETL. Vacuum, 2019, 159, 173-181.	3.5	42
96	GaN Silicon-on-Insulator (SOI) N-Channel FinFET for High-Performance Low Power Applications. , 2019, , .		5
97	Reliability Issues of In ₂ O ₅ Sn Gate Electrode Recessed Channel MOSFET: Impact of Interface Trap Charges and Temperature. IEEE Transactions on Electron Devices, 2018, 65, 860-866.	3.0	47
98	Temperature Associated Reliability Issues of Heterogeneous Gate Dielectric "Gate All Around" Tunnel FET. IEEE Nanotechnology Magazine, 2018, 17, 41-48.	2.0	34
99	Temperature Reliability of Junctionless Twin Gate Recessed Channel (JL-TGRC) MOSFET with Different Gate Material for Low Power Digital-Logic Applications. , 2018, , .		0
100	Parametric Variation of ZnSe/TiO ₂ Electron Transport Layer Based Perovskite Solar Cell: A Simulation Study and Optimization. , 2018, , .		2
101	Capacitive Analysis of Hetero Material Gate PNIN-DG-TFET Over Diverge Temperature Range for Superior RF/Microwave Performance. , 2018, , .		0
102	Electrical Characteristics Assessment of Gate Metal and Source Pocket Engineered DG-TFET for Low Power Analog Applications. , 2018, , .		3
103	Gate Drain Underlapping: A Performance Enhancer For HD-GAA-TFET. Materials Today: Proceedings, 2018, 5, 17453-17463.	1.8	13
104	Numerical Simulation of CeO _x ETL based Perovskite Solar Cell:- An Optimization Study for High Efficiency and Stability. , 2018, , .		3
105	Analysis of Varied Dielectrics as Surface Passivation on AlGaIn/GaN HEMT for Analog Applications. , 2018, , .		4
106	A moisture stable, hysteresis-free semi-transparent perovskite solar cell with single wall carbon nanotubes. , 2018, , .		1
107	Performance Analysis of Heterojunction DMDG-TFET with Different Source Materials for Analog Application. , 2018, , .		3
108	Heterojunction DG-TFET-Analysis of Different Source Material for Improved Intermodulation. , 2018, , .		3

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109	Source/Gate Material-Engineered Double Gate TFET for improved RF and linearity performance: a numerical simulation. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	34
110	Radiation Analysis of N-Channel TGRC-MOSFET: An X-Ray Dosimeter. IEEE Transactions on Electron Devices, 2018, 65, 5014-5020.	3.0	19
111	GaAs Junctionless FinFET Using High-k Dielectric for High-Performance Applications. , 2018, , .		3
112	Ultralow-power dielectric-modulated nanogap-embedded sub-20-nm TGRC-MOSFET for biosensing applications. Journal of Computational Electronics, 2018, 17, 1807-1815.	2.5	25
113	Investigation of Different Gate Materials for Improved Device Performance in RC MOSFET. , 2018, , .		1
114	Rear contact silicon solar cells with a-SiC _x H based front surface passivation for near-ultraviolet radiation stability. Superlattices and Microstructures, 2018, 122, 111-123.	3.1	6
115	Mathematical modeling insight of hetero gate dielectric-dual material gate-GAA-tunnel FET for VLSI/analog applications. Microsystem Technologies, 2017, 23, 4091-4098.	2.0	29
116	Quantum analysis based extraction of frequency dependent intrinsic and extrinsic parameters for GEWE-SiNW MOSFET. Journal of Computational Electronics, 2017, 16, 61-73.	2.5	1
117	Technology computer aided design of 29.5% efficient perovskite/interdigitated back contact silicon heterojunction mechanically stacked tandem solar cell for energy-efficient applications. Journal of Photonics for Energy, 2017, 7, 022503.	1.3	26
118	Numerical simulations of novel SiGe-based IBC-HJ solar cell for standalone and mechanically stacked tandem applications. Materials Research Bulletin, 2017, 93, 282-289.	5.2	22
119	Investigation of parasitic capacitances of In ₂ O ₅ Sn gate electrode recessed channel MOSFET for ULSI switching applications. Microsystem Technologies, 2017, 23, 5867-5874.	2.0	37
120	Numerical Simulation of N ⁺ Source Pocket PIN-GAA-Tunnel FET: Impact of Interface Trap Charges and Temperature. IEEE Transactions on Electron Devices, 2017, 64, 1482-1488.	3.0	84
121	Gate Drain Underlapped-PNIN-GAA-TFET for Comprehensively Upgraded Analog/RF Performance. Superlattices and Microstructures, 2017, 102, 17-26.	3.1	63
122	Performance investigation of heterogeneous gate dielectric-gate metal engineered gate all around-tunnel FET for RF applications. Microsystem Technologies, 2017, 23, 4081-4090.	2.0	23
123	Gate metal engineered heterojunction DG-TFETs for superior analog performance and enhanced device reliability. , 2017, , .		6
124	Source material assessment of heterojunction DG-TFET for improved analog performance. , 2017, , .		4
125	Reliability of high-k gate stack on transparent gate recessed channel (TGRC) MOSFET. , 2017, , .		1
126	Small-signal modeling of In ₂ O ₅ Sn based transparent gate recessed channel MOSFET for microwave/RF applications. , 2017, , .		4

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127	PNIN-GAA-tunnel FET with palladium catalytic metal gate as a highly sensitive hydrogen gas sensor. , 2017, , .		5
128	Interdigitated back contact silicon solar cell with perovskite layer for front surface passivation and ultraviolet radiation stability. , 2017, , .		0
129	Influence of gate metal engineering on small-signal and noise behaviour of silicon nanowire MOSFET for low-noise amplifiers. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	22
130	Rear contact SiGe solar cell with SiC passivated front surface for >90-percent external quantum efficiency and improved power conversion efficiency. Solar Energy, 2016, 135, 242-252.	6.1	20
131	Linearity performance of Gate Metal Engineered (GME) Omega Gate-Silicon Nanowire MOSFET: A TCAD study. , 2016, , .		3
132	Novel 4-terminal perovskite/SiC-based rear contact silicon tandem solar cell with 27.6 % PCE. , 2016, , .		4
133	Interfacial Charge Analysis of Heterogeneous Gate Dielectric-Gate All Around-Tunnel FET for Improved Device Reliability. IEEE Transactions on Device and Materials Reliability, 2016, 16, 227-234.	2.0	175
134	Numerical simulations: Toward the design of 27.6% efficient four-terminal semi-transparent perovskite/SiC passivated rear contact silicon tandem solar cell. Superlattices and Microstructures, 2016, 100, 656-666.	3.1	58
135	Numerical simulation of rear contact silicon solar cell with a novel front surface design for the suppression of interface recombination and improved absorption. Current Applied Physics, 2016, 16, 1581-1587.	2.4	23
136	Palladium Gate All Around - Hetero Dielectric -Tunnel FET based highly sensitive Hydrogen Gas Sensor. Superlattices and Microstructures, 2016, 100, 401-408.	3.1	27
137	Optimization of high-k and gate metal workfunction for improved analog and intermodulation performance of Gate Stack (GS)-GEWE-SiNW MOSFET. Superlattices and Microstructures, 2016, 97, 630-641.	3.1	47
138	Temperature associated reliability issues of heterogeneous gate dielectric-gate all around-tunnel FET. , 2016, , .		8
139	Gate drain-overlapped-asymmetric gate dielectric-GAA-TFET: a solution for suppressed ambipolarity and enhanced ON state behavior. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	44
140	Power gain assessment of ITO based Transparent Gate Recessed Channel (TGRC) MOSFET for RF/wireless applications. Superlattices and Microstructures, 2016, 91, 290-301.	3.1	32
141	Analysis of novel transparent gate recessed channel (TGRC) MOSFET for improved analog behaviour. Microsystem Technologies, 2016, 22, 2665-2671.	2.0	41
142	Oxide bound impact on hot-carrier degradation for gate electrode workfunction engineered (GEWE) silicon nanowire MOSFET. Microsystem Technologies, 2016, 22, 2655-2664.	2.0	10
143	Novel back-contact back-junction SiGe (BC-BJ SiGe) solar cell for improved power conversion efficiency. Microsystem Technologies, 2016, 22, 2673-2680.	2.0	18
144	Front Surface Passivation Scheme for Back-Contact Back-Junction (BC-BJ) Silicon Solar Cell. Advanced Science Letters, 2016, 22, 815-820.	0.2	4

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145	Novel SiC encapsulated coaxial silicon nanowire solar cell for optimal photovoltaic performance. , 2015, , .		3
146	Rear contact solar cell with ZrO ₂ nano structured front surface for efficient light trapping and enhanced surface passivation. , 2015, , .		3
147	Effect of dielectric engineering on analog and linearity performance of gate electrode workfunction engineered (GEWE) silicon nanowire MOSFET. , 2015, , .		4
148	Impact of device parameter variation on RF performance of gate electrode workfunction engineered (GEWE)-silicon nanowire (SiNW) MOSFET. Journal of Computational Electronics, 2015, 14, 798-810.	2.5	39
149	Implications of transport models on the analog performance of Gate Electrode Workfunction Engineered (GEWE) Silicon Nanowire MOSFET. , 2014, , .		6
150	Impact of Channel Doping and Gate Length on Small Signal Behaviour of Gate Electrode Workfunction Engineered Silicon Nanowire MOSFET at THz Frequency. , 2014, , .		2
151	Intermodulation distortion and linearity performance assessment of 50-nm gate length L-DUMGAC MOSFET for RFIC design. Superlattices and Microstructures, 2008, 44, 143-152.	3.1	27
152	Numerical simulations of a novel CH ₃ NH ₃ Pb ₃ based double-gate dopingless tunnel FET. Semiconductor Science and Technology, 0, , .	2.0	7